Discrete POWER & Signal **Technologies** 

# **MPSA29**

AIRCHILD SEMICONDUCTOR TM

MPSA29



### **NPN Darlington Transistor**

This device is designed for applications requiring extremely high current gain at collector currents to 500 mA. Sourced from Process 03. See MPSA28 for characteristics.

#### **Absolute Maximum Ratings\*** TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V <sub>CES</sub>	Collector-Emitter Voltage	100	V
V <sub>CBO</sub>	Collector-Base Voltage	100	V
V <sub>EBO</sub>	Emitter-Base Voltage	12	V
Ic	Collector Current - Continuous	800	mA
T <sub>J</sub> , T <sub>stg</sub>	Operating and Storage Junction Temperature Range	-55 to +150	°C

\*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

### NOTES:

1) These ratings are based on a maximum junction temperature of 150 degrees C.
 2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

### Thermal Characteristics

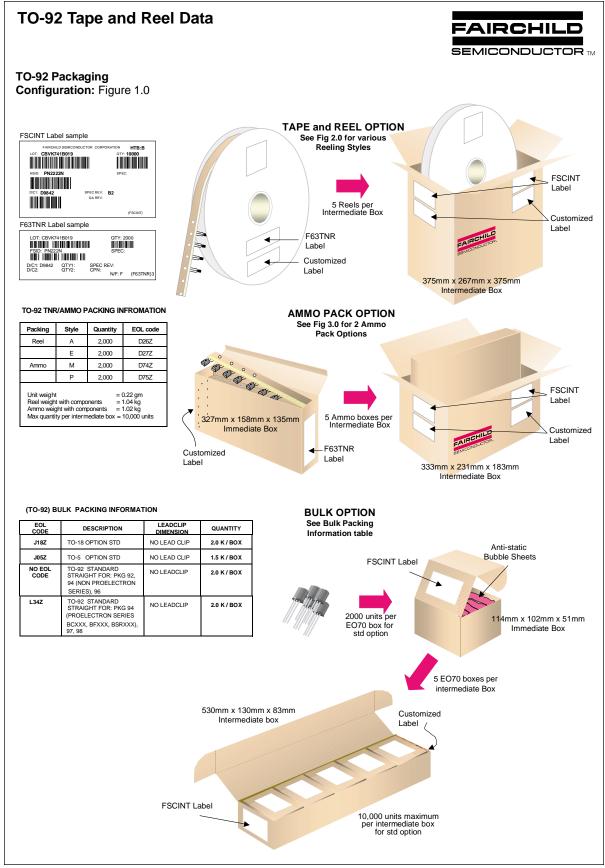
Thermal Characteristics         TA = 25°C unless otherwise noted					
Symbol	Characteristic	Max	Units		
		MPSA29			
P <sub>D</sub>	Total Device Dissipation	625	mW		
	Derate above 25°C	5.0	mW/°C		
$R_{\theta JC}$	Thermal Resistance, Junction to Case	83.3	°C/W		
$R_{ ext{ heta}JA}$	Thermal Resistance, Junction to Ambient	200	°C/W		

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## NPN Darlington Transistor (continued)

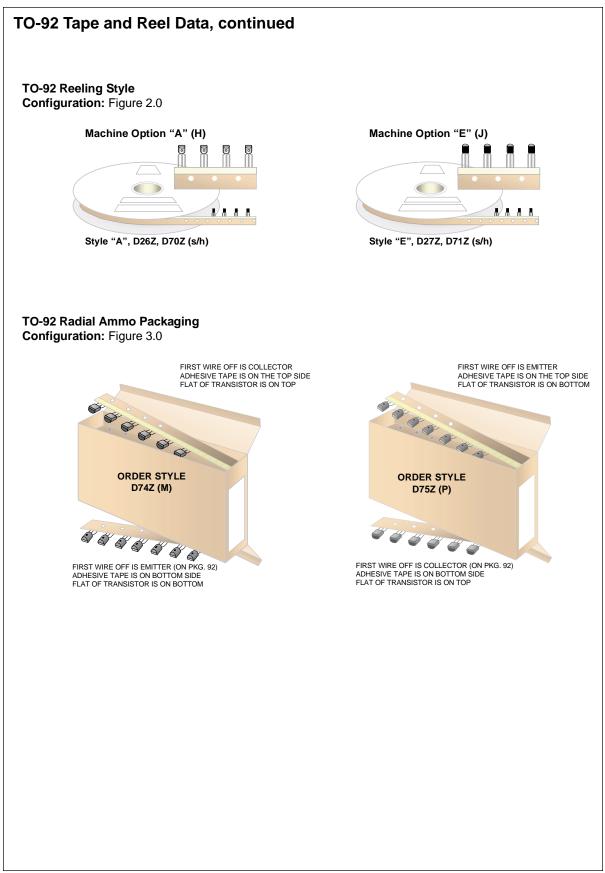
MPSA29

DF CHARACTERISTICS           (BR)CBD         Collector-Emitter Breakdown Voltage         I <sub>c</sub> = 100 µA, I <sub>b</sub> = 0         100         V           (BR)CBD         Collector-Base Breakdown Voltage         I <sub>c</sub> = 10 µA, I <sub>c</sub> = 0         12         V           (BR)EBD         Emitter-Base Breakdown Voltage         I <sub>c</sub> = 10 µA, I <sub>c</sub> = 0         12         V           (BR)EBD         Emitter-Base Breakdown Voltage         I <sub>c</sub> = 10 µA, I <sub>c</sub> = 0         12         V           (BR)EBD         Emitter-Base Breakdown Voltage         I <sub>c</sub> = 10 µA, I <sub>c</sub> = 0         120         N           (BR)EBD         Emitter-Base Breakdown Voltage         I <sub>c</sub> = 10 µA, I <sub>c</sub> = 0         1000         nA           (BR)EBD         Emitter-Cutoff Current         V <sub>CE</sub> = 80 V, I <sub>c</sub> = 0         1000         nA           (BO         Emitter Cutoff Current         V <sub>CE</sub> = 5.0 V, I <sub>c</sub> = 10 mA         10,000         nA           (BC         Current Gain         V <sub>CE</sub> = 5.0 V, I <sub>c</sub> = 10 mA, I <sub>b</sub> = 0.01 mA         1.2         V           (B(n)         Base-Emitter On Voltage         I <sub>c</sub> = 10 mA, V <sub>CE</sub> = 5.0 V         2.0         V           (BC(n)         Base-Emitter On Voltage         I <sub>c</sub> = 10 mA, V <sub>CE</sub> = 5.0 V,         125         MHz           (B(n)         Bandwidth Product         I <sub>c</sub> = 10 mA, V <sub>CE</sub> = 5.0	Collector-Emitter Breakdown Voltage* Collector-Base Breakdown Voltage Emitter-Base Breakdown Voltage	$I_{C} = 100 \ \mu A, I_{E} = 0$			V
$\begin{array}{c c c c c c c c c c c c c c c c c c c $	Collector-Emitter Breakdown Voltage* Collector-Base Breakdown Voltage Emitter-Base Breakdown Voltage	$I_{C} = 100 \ \mu A, I_{E} = 0$			V
$\begin{array}{c c c c c c c c c c c c c c c c c c c $	Collector-Base Breakdown Voltage Emitter-Base Breakdown Voltage	$I_{C} = 100 \ \mu A, I_{E} = 0$			V
$\begin{array}{c c c c c c c c c c c c c c c c c c c $	Emitter-Base Breakdown Voltage	-	100		V
BOCollector Cutoff Current $V_{CB} = 80 \text{ V}, I_E = 0$ 100nABOEmitter Cutoff Current $V_{CE} = 80 \text{ V}, I_E = 0$ 500nABOEmitter Cutoff Current $V_{EB} = 10 \text{ V}, I_C = 0$ 100nAON CHARACTERISTICS*FEDC Current Gain $V_{CE} = 5.0 \text{ V}, I_C = 10 \text{ mA}$ $V_{CE} = 5.0 \text{ V}, I_C = 100 \text{ mA}$ $I_C = 100 \text{ mA}, I_B = 0.01 \text{ mA}$ $I_C = 100 \text{ mA}, I_B = 0.1 \text{ mA}$ 1.2 $1.5 \text{ V}$ ON Collector-Emitter Saturation VoltageIC = 100 mA, I_B = 0.1 mAI.5 $V$ Base-Emitter On VoltageIC = 10 mA, $V_{CE} = 5.0 \text{ V}, I_C = 5.0 \text{ V}$ SMALL SIGNAL CHARACTERISTICSCurrent Gain - Bandwidth ProductI_C = 10 mA, $V_{CE} = 5.0 \text{ V}, I_C = 1.0 \text{ MHz}$ Source V_{CB} = 10 V, I_E = 0, f = 1.0 \text{ MHz}Source V_{CB} = 10 V, I_E = 0, f = 1.0 \text{ MHz}		$I_{\rm E} = 10  \text{uA}$ , $I_{\rm C} = 0$	40		
ESCollector Cutoff Current $V_{CE} = 80 \text{ V}, I_E = 0$ 500nABOEmitter Cutoff Current $V_{EB} = 10 \text{ V}, I_C = 0$ 100nAON CHARACTERISTICS*FEDC Current Gain $V_{CE} = 5.0 \text{ V}, I_C = 10 \text{ mA}$ 10,000 $CE(sat)$ Collector-Emitter Saturation Voltage $I_C = 10 \text{ mA}, I_B = 0.01 \text{ mA}$ 1.2V $I_C = 100 \text{ mA}, I_B = 0.1 \text{ mA}$ 1.5VV $BE(On)$ Base-Emitter On Voltage $I_C = 100 \text{ mA}, V_{CE} = 5.0 \text{ V}$ 2.0VSMALL SIGNAL CHARACTERISTICSCurrent Gain - Bandwidth Product $I_C = 10 \text{ mA}, V_{CE} = 5.0 \text{ V}, I_C = 1.0 \text{ MHz}$ $I_{Obo}$ Output Capacitance $V_{CB} = 10 \text{ V}, I_E = 0, f = 1.0 \text{ MHz}$ 8.0pF	Collector Cutorr Current		12	4.00	
BOEmitter Cutoff Current $V_{EB} = 10 \text{ V}, I_C = 0$ 100nAON CHARACTERISTICS*FEDC Current Gain $V_{CE} = 5.0 \text{ V}, I_C = 10 \text{ mA}$ 10,00010,000 $CE(sat)$ Collector-Emitter Saturation Voltage $I_C = 10 \text{ mA}, I_B = 0.01 \text{ mA}$ 1.2V $I_C = 100 \text{ mA}, I_B = 0.1 \text{ mA}$ 1.5V $I_C = 100 \text{ mA}, I_B = 0.1 \text{ mA}$ 1.5V $BE(on)$ Base-Emitter On Voltage $I_C = 100 \text{ mA}, V_{CE} = 5.0 \text{ V}$ 2.0VSMALL SIGNAL CHARACTERISTICSCurrent Gain - Bandwidth Product $I_C = 10 \text{ mA}, V_{CE} = 5.0 \text{ V}, f = 100 \text{ MHz}$ 125MHzGutput Capacitance $V_{CB} = 10 \text{ V}, I_E = 0, f = 1.0 \text{ MHz}$ 8.0pF	Collector Cutoff Current		+		
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DC Current Gain $V_{CE} = 5.0 \text{ V}, I_C = 10 \text{ mA}$ 10,000         10,000 $C_{CE(sat)}$ Collector-Emitter Saturation Voltage $I_C = 10 \text{ mA}, I_B = 0.01 \text{ mA}$ 1.2         V $I_C = 100 \text{ mA}, I_B = 0.1 \text{ mA}$ 1.5         V $BE(on)$ Base-Emitter On Voltage $I_C = 100 \text{ mA}, V_{CE} = 5.0 \text{ V}$ 2.0         V           SMALL SIGNAL CHARACTERISTICS         Current Gain - Bandwidth Product $I_C = 10 \text{ mA}, V_{CE} = 5.0 \text{ V}, f = 100 \text{ MHz}$ 125         MHz           fobo         Output Capacitance $V_{CB} = 10 \text{ V}, I_E = 0, f = 1.0 \text{ MHz}$ 8.0         pF		$v_{EB} = 10 v, i_C = 0$		100	IIA
V <sub>CE</sub> = 5.0 V, I <sub>C</sub> = 100 mA10,000 $C_{CE(sat)}$ Collector-Emitter Saturation VoltageI <sub>C</sub> = 10 mA, I <sub>B</sub> = 0.01 mA1.2VI <sub>C</sub> = 100 mA, I <sub>B</sub> = 0.1 mA1.5VBase-Emitter On VoltageI <sub>C</sub> = 100 mA, V <sub>CE</sub> = 5.0 V2.0VSMALL SIGNAL CHARACTERISTICSCurrent Gain - Bandwidth ProductI <sub>C</sub> = 10 mA, V <sub>CE</sub> = 5.0 V, f = 100 MHz125MHzStoboOutput CapacitanceV <sub>CB</sub> = 10 V, I <sub>E</sub> = 0, f = 1.0 MHz8.0pF	ACTERISTICS*				-
$\begin{tabular}{ c c c c c c c c c c c c c c c c c c c$	DC Current Gain				
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SMALL SIGNAL CHARACTERISTICS         Current Gain - Bandwidth Product $I_C = 10 \text{ mA}, V_{CE} = 5.0 \text{ V}, \\ f = 100 \text{ MHz}$ 125       MHz         Nobo       Output Capacitance $V_{CB} = 10 \text{ V}, I_E = 0, f = 1.0 \text{ MHz}$ 8.0       pF		$I_{\rm C} = 100 \text{ mA}, I_{\rm B} = 0.1 \text{ mA}$			
Current Gain - Bandwidth Product $I_C = 10 \text{ mA}, V_{CE} = 5.0 \text{ V}, f = 100 \text{ MHz}$ 125MHzNoboOutput Capacitance $V_{CB} = 10 \text{ V}, I_E = 0, f = 1.0 \text{ MHz}$ 8.0pF	Base-Emitter On Voltage	$I_{\rm C} = 100 \text{ mA}, V_{\rm CE} = 5.0 \text{ V}$		2.0	V
*Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%	Output Capacitance			8.0	pF
		DC Current Gain Collector-Emitter Saturation Voltage Base-Emitter On Voltage GNAL CHARACTERISTICS Current Gain - Bandwidth Product Output Capacitance	$\label{eq:constraint} \begin{array}{llllllllllllllllllllllllllllllllllll$	$ \begin{array}{c c} DC \ Current \ Gain & V_{CE} = 5.0 \ V, \ I_{C} = 10 \ mA & 10,000 \\ V_{CE} = 5.0 \ V, \ I_{C} = 100 \ mA & 10,000 \\ \hline V_{CE} = 5.0 \ V, \ I_{C} = 100 \ mA & 10,000 \\ \hline I_{C} = 100 \ mA, \ I_{B} = 0.01 \ mA & I_{C} = 100 \ mA, \ I_{B} = 0.1 \ mA & I_{C} = 100 \ mA, \ I_{B} = 0.1 \ mA & I_{C} = 100 \ mA, \ V_{CE} = 5.0 \ V \\ \hline \end{array} $	DC Current Gain $V_{CE} = 5.0 \text{ V}, I_C = 10 \text{ mA}$ 10,000 $V_{CE} = 5.0 \text{ V}, I_C = 100 \text{ mA}$ 10,000           Collector-Emitter Saturation Voltage $I_C = 10 \text{ mA}, I_B = 0.01 \text{ mA}$ 1.2 $I_C = 100 \text{ mA}, I_B = 0.1 \text{ mA}$ 1.5         1.5           Base-Emitter On Voltage $I_C = 100 \text{ mA}, V_{CE} = 5.0 \text{ V}$ 2.0           SNAL CHARACTERISTICS           Current Gain - Bandwidth Product $I_C = 10 \text{ mA}, V_{CE} = 5.0 \text{ V}, f = 100 \text{ MHz}$ 125           Output Capacitance $V_{CB} = 10 \text{ V}, I_E = 0, f = 1.0 \text{ MHz}$ 8.0

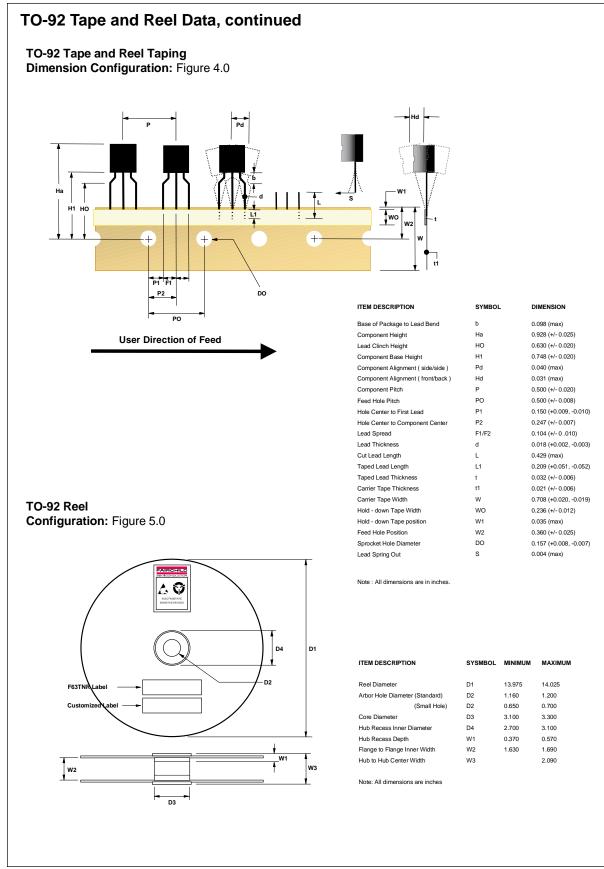


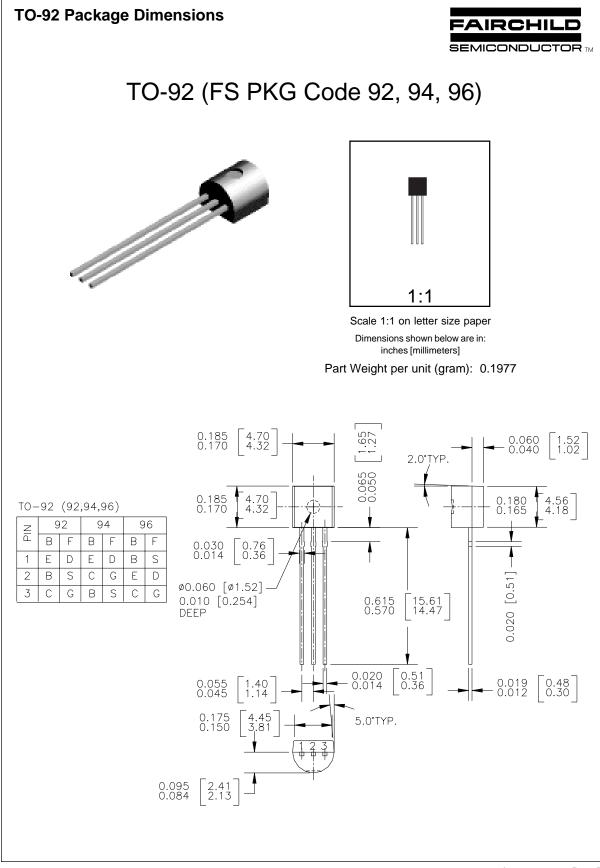
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Definition of Terms

Product Status	Definition
Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
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